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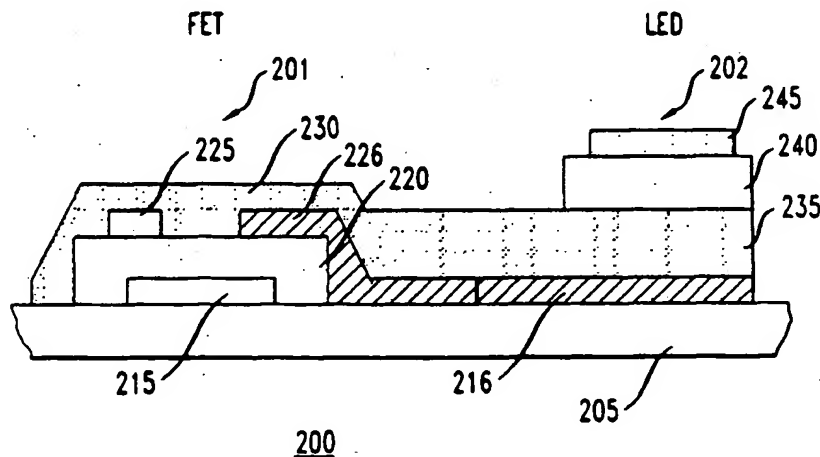
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(54) **Thin-film transistor monolithically integrated with an organic light-emitting diode**

(57) A device in which one or more thin film transistors are monolithically integrated with a light emitting diode is disclosed. The thin film transistor has an organic semiconductor layer. The light emitting layer of the light

emitting diode is also an organic material. The device is fabricated economically by integrating the fabrication of the thin film transistor and the light emitting diode on the substrate and by employing low cost fabrication techniques.

FIG. 2



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